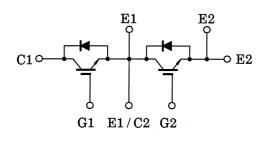
TOSHIBA GTR Module Silicon N Channel IGBT

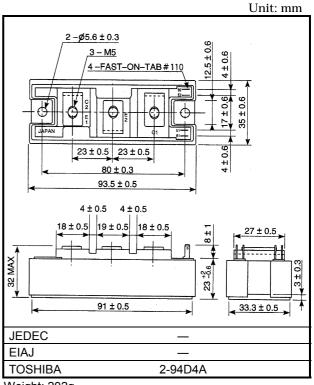
MG75Q2YS50

High Power Switching Applications Motor Control Applications

- High input impedance
- High speed : $t_f = 0.3 \ \mu s$ (Max) @Iinductive load
- Low saturation voltage
- : $V_{CE (sat)} = 3.6 V (Max)$
- Enhancement-mode
- Includes a complete half bridge in one package
- The electrodes are Isolated from case

Equivalent Circuit





Weight: 202g

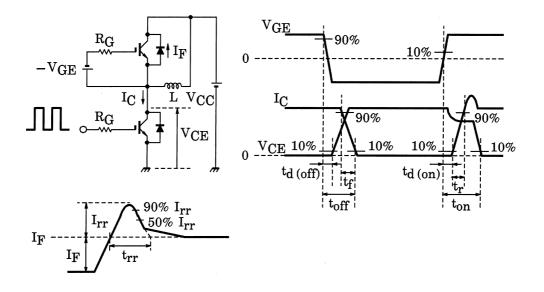
Maximum Ratings (Ta = 25°C)

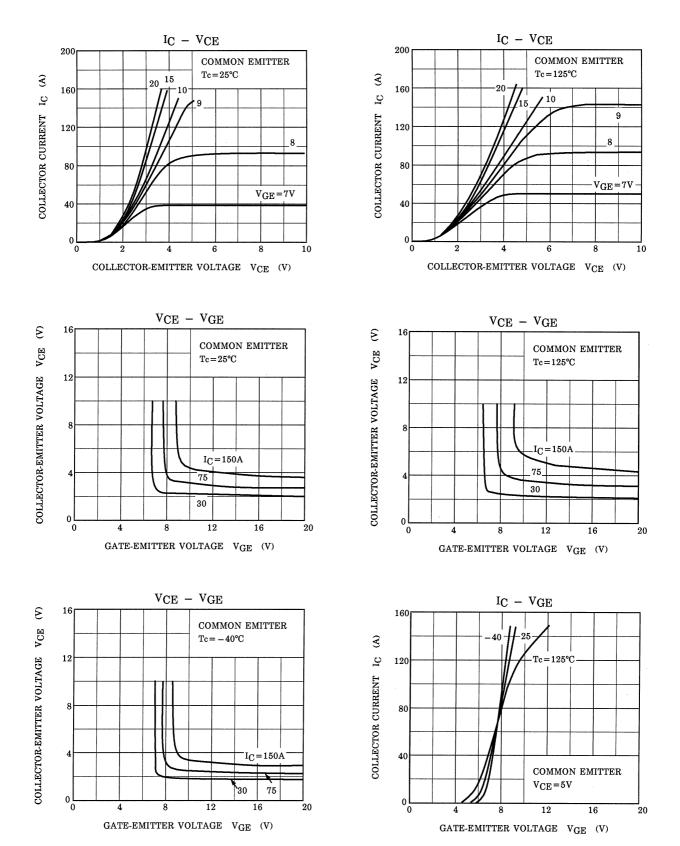
Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	l _C (25°C / 80°C)	100 / 75	А	
	1ms	I _{CP} (25°C / 80°C)	200 / 150	A	
Forward current	DC	١ _F	75	A	
	1ms	I _{FM}	150		
Collector power dissipation (Tc = 25°C)		PC	600	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1minute)	V	
Screw torque (Terminal / mounting)		—	3/3	N∙m	

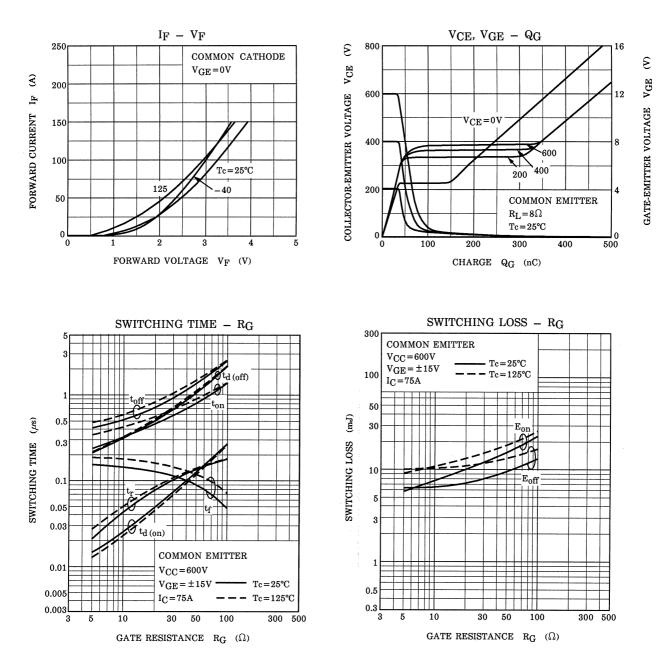
Electrical Characteristics (Ta = 25°C)

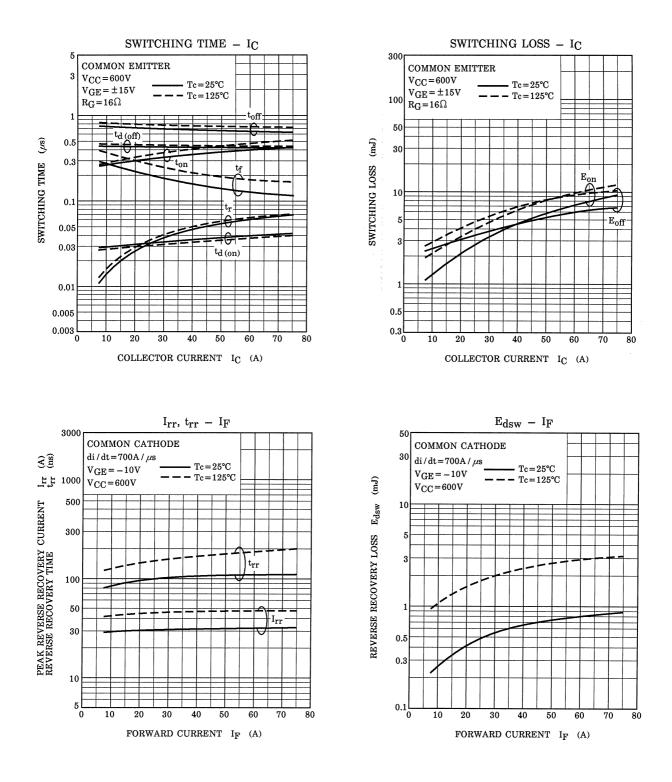
Ch	Characteristic Symbol Test Condition		on	Min	Тур.	Max	Unit	
Gate leakage current		I _{GES}	V _{GE} = ±20 V, V _{CE} = 0		_	—	±500	nA
Collector cut-off current		ICES	V _{CE} = 1200 V, V _{GE} = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 75 mA, V _{CE} = 5 V		3.0	_	6.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 75 A,V _{GE} = 15 V	T _j = 25°C	_	2.8	3.6	V
				T _j = 125°C	_	3.1	4.0	
Input capacitance	9	C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz		_	8.5	_	nF
Switching time	Turn-on delay time	t _{d (on)}	Inductive load $V_{CC} = 600 V$ $I_C = 75 A$ $V_{GE} = \pm 15 V$ $R_G = 16 \Omega$		_	0.05	_	
	Rise-time	tr			_	0.05	_	μs
	Turn-on time	t _{on}			_	0.2	_	
	Turn-off delay time	t _{d (off)}		(Note 1)	_	0.5	_	
	Fall time	t _f			_	0.1	0.3	
	Turn-off time	t _{off}			_	0.6	_	
Forward voltage		VF	I _F = 75 A, V _{GE} = 0		_	2.4	3.5	V
Reverse recovery time		t _{rr}	I _F = 75 A, V _{GE} = -10 V di / dt = 700 A / μs (Note 1)		_	0.1	0.25	μs
Thermal resistance		R _{th (j-c)}	Transistor stage		_	_	0.2	°C/W
			Diode stage	Diode stage			0.47	

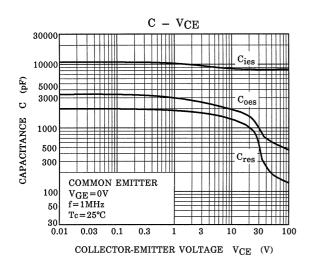
Note 1: Switching time and reverse recovery time test circuit & timing chart

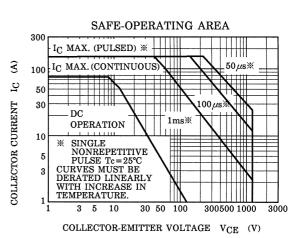


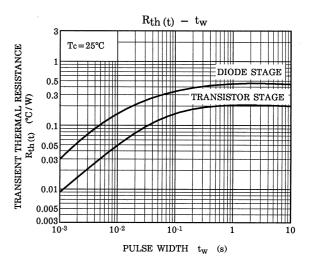


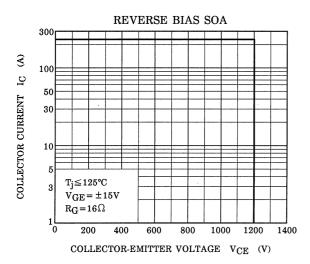


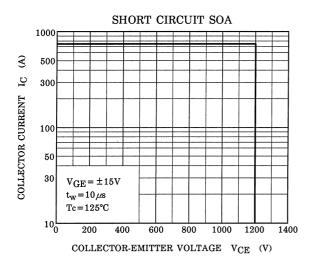












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